



PATENT  
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**IN THE U.S. PATENT AND TRADEMARK OFFICE**

Applicant: YANG, Hae C. Conf. No.: 1780  
Appl. No.: 09/452,809 Group: 2814  
Filed: December 2, 1999 Examiner: Dana Farahani  
For: ESD PROTECTION CIRCUIT AND METHOD FOR  
FABRICATING THE SAME

**AMENDMENT**

Honorable Commissioner of Patents  
Washington, D.C. 20231

May 10, 2002

Sir:

In response to the Examiner's Office Action dated February 11, 2002, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

**In the Specification:**

Please replace the paragraph beginning on page 1, line 7, with the following rewritten paragraph:

*B'* Fig. 1 illustrates a system of a related art ESD protection circuit. In general, a maximum field strength against which an oxide film in an MOS transistor can endure is 6MV/cm, which corresponds to 30V if the oxide film is scaled up to a thickness of 50nm. A voltage of this magnitude can be easily